

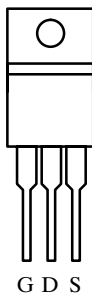
N-Channel Enhancement-Mode Transistors

Product Summary

$V_{(BR)DSS}$ (V)	$r_{DS(on)}$ (Ω)	I_D (A)
75	0.010	75 ^a

175°C Rated
Maximum Junction Temperature

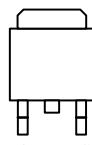
TO-220AB



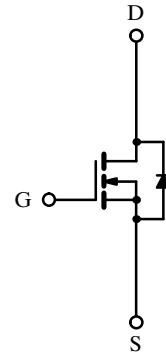
Top View
SUP75N08-10

DRAIN connected to TAB

TO-263



Top View
SUB75N08-10



N-Channel MOSFET

Absolute Maximum Ratings ($T_C = 25^\circ\text{C}$ Unless Otherwise Noted)

Parameter	Symbol	Limit	Unit
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current ($T_J = 175^\circ\text{C}$)	I_D	$T_C = 25^\circ\text{C}$	75 ^a
		$T_C = 125^\circ\text{C}$	55
Pulsed Drain Current	I_{DM}	240	A
Avalanche Current	I_{AR}	60	
Repetitive Avalanche Energy ^b	E_{AR}	280	mJ
Power Dissipation	P_D	$T_C = 25^\circ\text{C}$ (TO-220AB and TO-263)	187 ^c
		$T_A = 25^\circ\text{C}$ (TO-263) ^d	3.7
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55 to 175	$^\circ\text{C}$

Thermal Resistance Ratings

Parameter	Symbol	Limit	Unit
Junction-to-Ambient	R_{thJA}	PCB Mount (TO-263) ^d	40
		Free Air (TO-220AB)	62.5
Junction-to-Case	R_{thJC}	0.8	$^\circ\text{C/W}$

Notes

- a. Package limited.
- b. Duty cycle $\leq 1\%$.
- c. See SOA curve for voltage derating.
- d. When mounted on 1" square PCB (FR-4 material).

Updates to this data sheet may be obtained via facsimile by calling Siliconix FaxBack, 1-408-970-5600. Please request FaxBack document #70263.

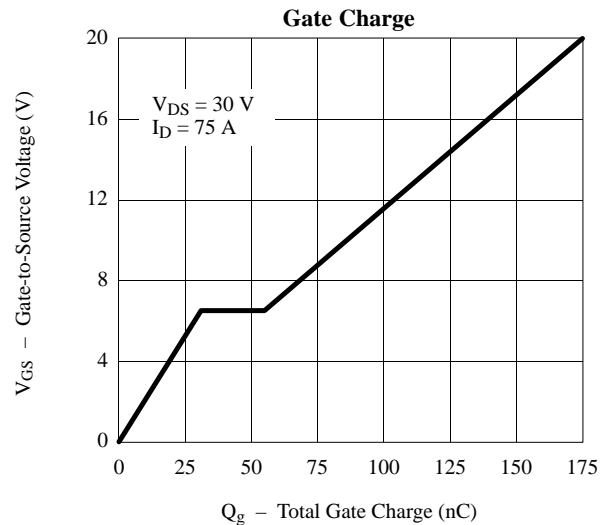
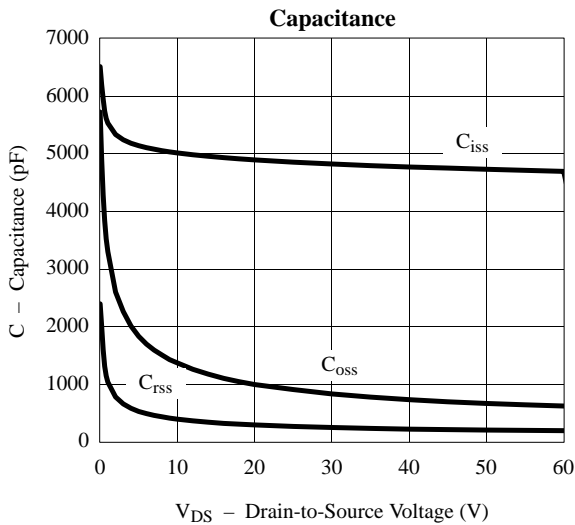
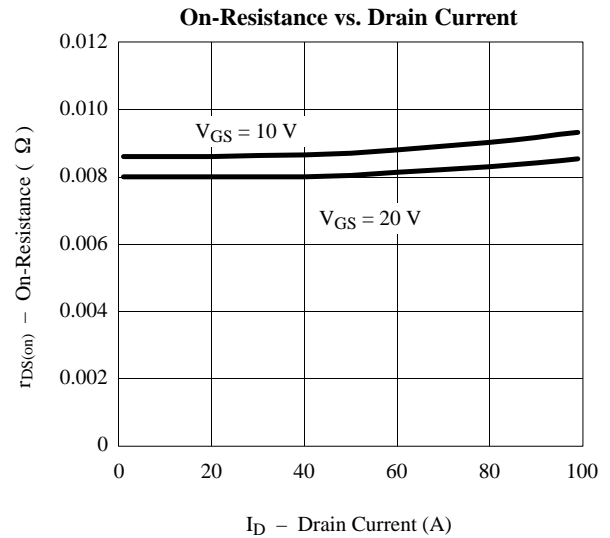
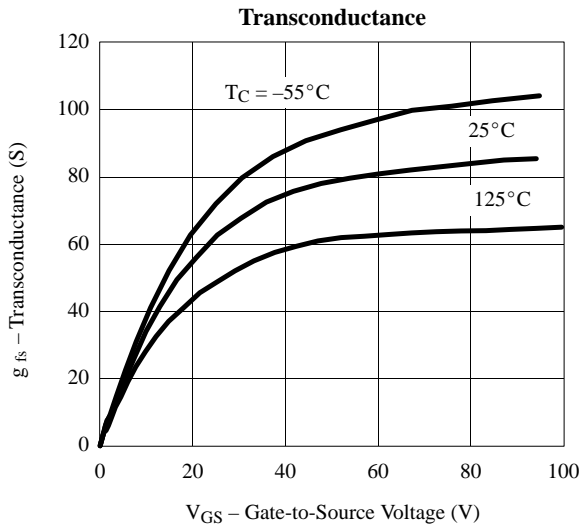
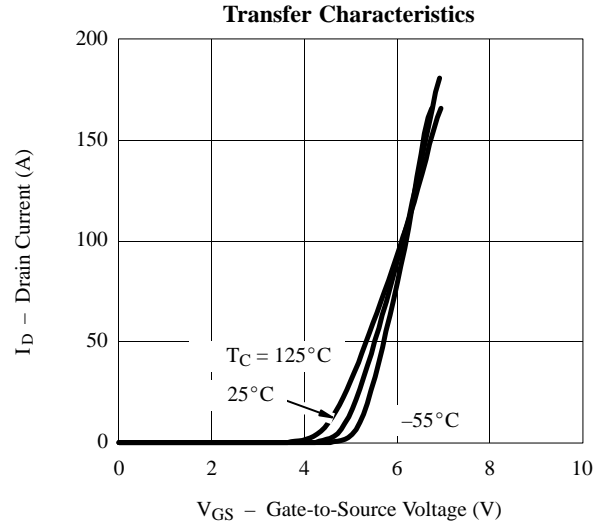
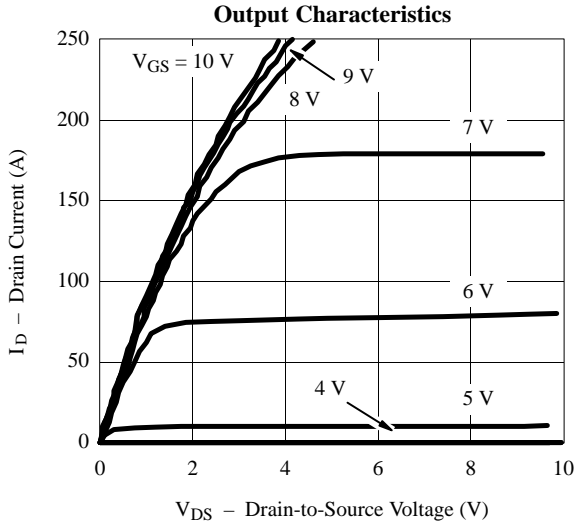
Specifications ($T_J = 25^\circ\text{C}$ Unless Otherwise Noted)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}, I_D = 250\ \mu\text{A}$	75			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\ \mu\text{A}$	2.0	3.5	4.5	
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 75\text{ V}, V_{GS} = 0\text{ V}$			1	μA
		$V_{DS} = 75\text{ V}, V_{GS} = 0\text{ V}, T_J = 125^\circ\text{C}$			50	
		$V_{DS} = 75\text{ V}, V_{GS} = 0\text{ V}, T_J = 175^\circ\text{C}$			150	
On-State Drain Current ^b	$I_{D(on)}$	$V_{DS} = 5\text{ V}, V_{GS} = 10\text{ V}$	120			A
Drain-Source On-State Resistance ^b	$r_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 30\text{ A}$		0.0087	0.010	Ω
		$V_{GS} = 10\text{ V}, I_D = 30\text{ A}, T_J = 125^\circ\text{C}$			0.017	
		$V_{GS} = 10\text{ V}, I_D = 30\text{ A}, T_J = 175^\circ\text{C}$			0.021	
Forward Transconductance ^b	g_{fs}	$V_{DS} = 15\text{ V}, I_D = 30\text{ A}$	30			S
Dynamic^a						
Input Capacitance	C_{iss}	$V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1\text{ MHz}$		4800		pF
Output Capacitance	C_{oss}			910		
Reverse Transfer Capacitance	C_{rss}			270		
Total Gate Charge ^c	Q_g	$V_{DS} = 30\text{ V}, V_{GS} = 10\text{ V}, I_D = 75\text{ A}$		85	120	nC
Gate-Source Charge ^c	Q_{gs}			31		
Gate-Drain Charge ^c	Q_{gd}			24		
Turn-On Delay Time ^c	$t_{d(on)}$	$V_{DD} = 30\text{ V}, R_L = 0.47\ \Omega$ $I_D \cong 75\text{ A}, V_{GEN} = 10\text{ V}, R_G = 2.5\ \Omega$		20	40	ns
Rise Time ^c	t_r			95	200	
Turn-Off Delay Time ^c	$t_{d(off)}$			65	120	
Fall Time ^c	t_f			20	60	
Source-Drain Diode Ratings and Characteristics ($T_C = 25^\circ\text{C}$)^a						
Continuous Current	I_S				75	A
Pulsed Current	I_{SM}				240	
Forward Voltage ^b	V_{SD}	$I_F = 75\text{ A}, V_{GS} = 0\text{ V}$		1.0	1.3	V
Reverse Recovery Time	t_{rr}	$I_F = 75\text{ A}, di/dt = 100\text{ A}/\mu\text{s}$		80	120	ns
Peak Reverse Recovery Current	$I_{RM(REC)}$			7	9	A
Reverse Recovery Charge	Q_{rr}			0.28	0.54	μC

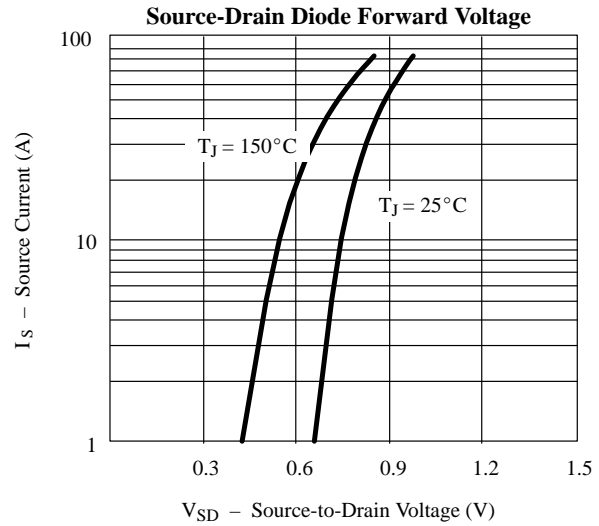
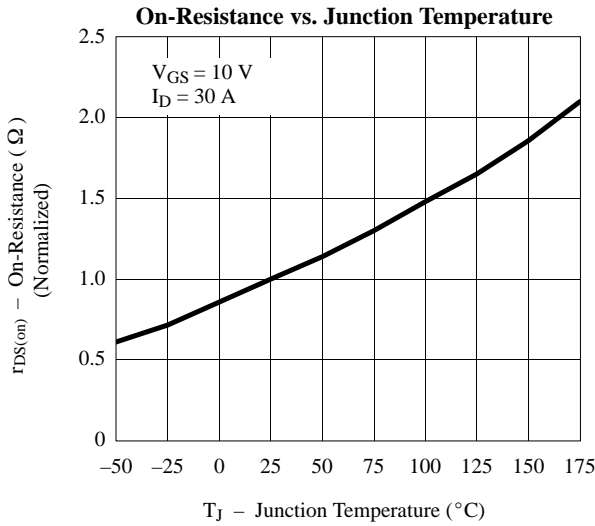
Notes

- Guaranteed by design, not subject to production testing.
- Pulse test: pulse width $\leq 300\ \mu\text{sec}$, duty cycle $\leq 2\%$.
- Independent of operating temperature.

Typical Characteristics (25°C Unless Otherwise Noted)



Typical Characteristics (25°C Unless Otherwise Noted)



Thermal Ratings

